L Number	Hits	Search Text	DB	Time stamp
3	1422619	semiconductor	USPAT;	2004/11/08 14:17
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/11/00 12 07
4	424825	LED\$1 near3 chip) (light\$3 near3 emitt\$3	USPAT;	2004/11/08 13:27
1		· \	US-PGPUB;	
		*	EPO; JPO; DERWENT;	
			IBM TDB	
5	426835	LED\$1 with chip) (light\$3 near3 emitt\$3	USPAT;	2004/11/08 13:27
	120000	LEBYT WICH ONLY, (IIGHEYO HOULD OMICOYO	US-PGPUB;	=====================================
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	94753		USPAT;	2004/11/08 13:27
		(light\$3 near3 emitt\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
-	1.6027	(GaN miturida) 6 (anni annimatan 6 (IRDC)	IBM_TDB	2004/11/00 14:10
7	16037		USPAT;	2004/11/08 14:18
		near3 chip) (light\$3 near3 emitt\$3))	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
8	1843	((GaN nitride) & (semiconductor & (LED\$1	USPAT;	2004/11/08 14:19
	10.0	near3 chip) (light\$3 near3 emitt\$3))) &	US-PGPUB;	
		(thermal near3 expansion)	EPO; JPO;	
		•	DERWENT;	
			IBM_TDB	
9	503	, , , , ,	USPAT;	2004/11/08 13:40
		near3 chip) (light\$3 near3 emitt\$3))) &	US-PGPUB;	
		(thermal near3 expansion)) & solder\$3	EPO; JPO;	
			DERWENT;	
10	463	(///CaN mitmide) [(comicanductor [(IED\$1	IBM_TDB USPAT;	2004/11/08 13:40
10	463	(((((GaN nitride) & (semiconductor & (LED\$1 near3 chip) (light\$3 near3 emitt\$3))) &	US-PGPUB;	2004/11/08 13:40
		(thermal near3 expansion)) & solder\$3) &	EPO; JPO;	•
		substrate	DERWENT;	
			IBM TDB	
11	371	(((((GaN nitride) & (semiconductor &	USPĀT;	2004/11/08 13:29
		(LED\$1 near3 chip) (light\$3 near3	US-PGPUB;	j
		emitt\$3))) & (thermal near3 expansion)) &	EPO; JPO;	
		solder\$3) & substrate) & higher	DERWENT;	
10	20		IBM_TDB	0004/11/00 13:30
12	39	((((((GaN nitride) & (semiconductor &	USPAT;	2004/11/08 13:38
		(LED\$1 near3 chip) (light\$3 near3 emitt\$3))) & (thermal near3 expansion)) &	US-PGPUB; EPO; JPO;	,
1		solder\$3) & substrate) & higher) &	DERWENT;	
		((thermal near3 expansion) with higher)	IBM TDB	
13	90		USPAT;	2004/11/08 13:39
		substrate))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
14	81		USPAT;	2004/11/08 13:39
	1	& (semiconductor & (chip with (GaN near5	US-PGPUB;	
		substrate)))	EPO; JPO;	
			DERWENT; IBM TDB	
15	28	((LED\$1 with chip) (light\$3 near3 emitt\$3)	USPAT;	2004/11/08 13:40
~~		& (semiconductor & (chip with (GaN near5	US-PGPUB;	
		substrate)))) & (thermal near3 expansion)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	28		USPĀT;	2004/11/08 13:40
1		emitt\$3) & (semiconductor & (chip with	US-PGPUB;	
		(GaN near5 substrate)))) & (thermal near3	EPO; JPO;	
		expansion)) & substrate	DERWENT;	
	l		IBM TDB	<u> </u>

17	11	((((LED\$1 with chip) (light\$3 near3 emitt\$3) & (semiconductor & (chip with	USPAT; US-PGPUB;	2004/11/08 13:49
		(GaN near5 substrate)))) & (thermal near3	EPO; JPO;	
		expansion)) & substrate) & solder\$3	DERWENT; IBM TDB	'
18	6		USPĀT;	2004/11/08 13:52
	ļ	& (semiconductor & (chip with (GaN near5 substrate)))) & ((mount\$3 submount\$3) with	US-PGPUB; EPO; JPO;	
		(thermal near3 expansion) with substrate)	DERWENT;	
19	8	((LED\$1 with chip) (light\$3 near3 emitt\$3)	IBM_TDB USPAT;	2004/11/08 13:56
19	°	& (semiconductor & (chip with (GaN near5	US-PGPUB;	2004/11/00 15.50
		substrate)))) & ((mount\$3 submount\$3) same	EPO; JPO;	
		(thermal near3 expansion) same substrate)	DERWENT; IBM TDB	
20	9		USPAT;	2004/11/08 13:58
		<pre>substrate))) & ((mount\$3 submount\$3) same (thermal near3 expansion) same substrate)</pre>	US-PGPUB; EPO; JPO;	
		,	DERWENT;	
21	22	(semiconductor & (chip with (GaN near5	IBM_TDB USPAT;	2004/11/08 14:17
		substrate))) & ((mount\$3 submount\$3) &	US-PGPUB;	2001/11/00 1111/
		(thermal near3 expansion) & substrate)	EPO; JPO; DERWENT;	
			IBM_TDB	
22	127803	semiconductor with laser	USPAT; US-PGPUB;	2004/11/08 14:17
			EPO; JPO;	
			DERWENT; IBM TDB	
23	5486	((GaN nitride) with substrate) &	USPAT;	2004/11/08 14:36
		(semiconductor with laser)	US-PGPUB;	
			EPO; JPO; DERWENT;	
2.4	4157	//CaN situida) sasu? substrata) s	IBM_TDB	2004/11/00 14.41
24	4157	((GaN nitride) near7 substrate) & (semiconductor with laser)	USPAT; US-PGPUB;	2004/11/08 14:41
			EPO; JPO;	
			DERWENT; IBM TDB	
25	658	(((GaN nitride) near7 substrate) &	USPAT;	2004/11/08 14:19
		(semiconductor with laser)) & (thermal near3 expansion)	US-PGPUB; EPO; JPO;	
			DERWENT;	
26	15	(((GaN nitride) near7 substrate) &	IBM_TDB USPAT;	2004/11/08 14:37
		(semiconductor with laser)) & ((thermal	US-PGPUB;	
	,	near3 expansion) with higher with substrate)	EPO; JPO; DERWENT;	
27	10242	((C-N = i to i do)	IBM_TDB	2004/11/00 14:27
21	10242	((GaN nitride) & substrate) & (semiconductor with laser)	USPAT; US-PGPUB;	2004/11/08 14:37
			EPO; JPO;	
			DERWENT; IBM TDB	
28	0	(((GaN nitride) & substrate) &	USPAT;	2004/11/08 14:38
		(semiconductor with laser)) & ((thermal near3 expansion) with (higher near7 than)	US-PGPUB; EPO; JPO;	
		with substrate)	DERWENT;	
29	0	(semiconductor with laser) & ((thermal	IBM_TDB USPAT;	2004/11/08 14:39
		near3 expansion) with (higher near7 than)	US-PGPUB;	
		with substrate)	EPO; JPO; DERWENT;	
30	0	comiconductor (//thormal near)	IBM_TDB USPAT;	2004/11/08 14:39
30		semiconductor & ((thermal near3 expansion) with (higher near7 than) with substrate)	US-PGPUB;	2004/11/08 14:39
			EPO; JPO;	
L			DERWENT; IBM_TDB	
				

31	0	((thermal near3 expansion) with (higher near7 than) with substrate)	USPAT; US-PGPUB; EPO; JPO;	2004/11/08 14:40
			DERWENT;	
32	0	((thermal near3 expansion) with (higher adj than) with substrate)	IBM_TDB USPAT; US-PGPUB;	2004/11/08 14:40
			EPO; JPO; DERWENT; IBM_TDB	
33	824	((thermal near3 expansion) with (higher) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/08 14:40
34	49	(semiconductor with laser) & (((thermal near3 expansion) with (higher) with substrate))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/11/08 14:40
			DERWENT; IBM TDB	
35	15	((GaN nitride) near7 substrate) & ((semiconductor with laser) & ((thermal near3 expansion) with (higher) with	USPAT; US-PGPUB; EPO; JPO;	2004/11/08 14:41
		substrate)))	DERWENT;	
_	1422619	semiconductor	IBM_TDB USPAT; US-PGPUB;	2004/11/07 17:14
			EPO; JPO; DERWENT; IBM TDB	
-	500623	LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device))	USPAT; US-PGPUB; EPO; JPO;	2004/11/07 17:16
			DERWENT;	
_	79815	semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/11/07 17:16
			DERWENT;	
_	33299	(semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & laser	IBM_TDB USPAT; US-PGPUB;	2004/11/07 17:17
		·	EPO; JPO; DERWENT;	
_	3281	semiconductor near3 laser near3 chip	IBM_TDB USPAT; US-PGPUB;	2004/11/07 17:17
			EPO; JPO; DERWENT; IBM TDB	
_	708	((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) & laser) & (semiconductor near3 laser near3 chip)	USPAT; US-PGPUB; EPO; JPO;	2004/11/07 17:18
			DERWENT; IBM TDB	
_	41968	emitt\$3 near3 (diod\$3 device)))) &	USPAT; US-PGPUB;	2004/11/07 17:19
		substrat\$3	EPO; JPO; DERWENT; IBM TDB	
_	11793	emitt\$3 near3 (diod\$3 device)))) &	USPAT; US-PGPUB;	2004/11/07 17:45
		substrat\$3) & nitride	EPO; JPO; DERWENT; IBM TDB	
-	157	emitt\$3 near3 (diod\$3 device)))) &	USPAT; US-PGPUB;	2004/11/07 17:20
		substrat\$3) & nitride) & (substrat\$3 with (thermal near3 expans\$4) with high\$3)	EPO; JPO; DERWENT; IBM_TDB	
·		A CONTRACTOR OF THE PROPERTY O		

-	156	((((semiconductor & (LED\$1 (light\$3 near3	USPAT; US-PGPUB;	2004/11/07 17:23
		emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride) & (substrat\$3 with	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) &	DERWENT;	
	4.7	(layer\$1 stack\$3 chip\$3)	IBM_TDB	2004/11/07 17:45
_	41	<pre>((((((semiconductor & (LED\$1 (light\$3 near3 emitt\$3 near3 (diod\$3 device)))) &</pre>	USPAT; US-PGPUB;	2004/11/0/ 1/:45
		substrat\$3) & nitride) & (substrat\$3 with	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) &	DERWENT;	
_	7	(layer\$1 stack\$3 chip\$3)) & solder\$3 (((((semiconductor & (LED\$1 (light\$3 near3	IBM_TDB USPAT;	2004/11/07 17:47
-	, ,	emitt\$3 near3 (diod\$3 device)))) &	US-PGPUB;	2004/11/07 17:47
		substrat\$3) & nitride) & (substrat\$3 with	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) & solder\$3) & ((nitri\$3 near3 bas\$3)	DERWENT; IBM TDB	
		nitridebased)	1211_122	
-	7	(((((semiconductor & (LED\$1 (light\$3 near3	USPAT;	2004/11/07 17:47
'		<pre>emitt\$3 near3 (diod\$3 device)))) & substrat\$3) & nitride) & (substrat\$3 with</pre>	US-PGPUB; EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) &	DERWENT;	
		solder\$3) & ((nitri\$3 near3 bas\$3)	IBM_TDB	
	41	<pre>(nitride-based)) ((((semiconductor & (LED\$1 (light\$3 near3</pre>	USPAT;	2004/11/08 10:46
	41	emitt\$3 near3 (diod\$3 device)))) &	US-PGPUB;	2004/11/00 10:40
		substrat\$3) & nitride) & (substrat\$3 with	EPO; JPO;	
		(thermal near3 expans\$4) with high\$3)) & solder\$3	DERWENT; IBM TDB	
_	1441160	semiconductor\$3	USPAT;	2004/11/08 10:47
			US-PGPUB;	
			EPO; JPO; DERWENT;	·
			IBM_TDB	
_	422761	light\$3 near3 emitt\$3	USPAT;	2004/11/08 10:48
			US-PGPUB; EPO; JPO;	
			DERWENT;	
	05000		IBM_TDB	2004/11/08 10:48
_	95809	semiconductor\$3 & (light\$3 near3 emitt\$3)	USPAT; US-PGPUB;	2004/11/08 10:48
			EPO; JPO;	
			DERWENT; IBM TDB	
_	493	(semiconductor\$3 & (light\$3 near3	USPAT;	2004/11/08 10:49
		emitt\$3)) & (higher same (thermal near3	US-PGPUB;	
		expansion))	EPO; JPO; DERWENT;	
			IBM_TDB	
-	140	, ,	USPĀT;	2004/11/08 10:52
		<pre>emitt\$3)) & (higher same (thermal near3 expansion))) & (GaN (nitride adj bas\$3))</pre>	US-PGPUB; EPO; JPO;	
			DERWENT;	
	136	///amigandushan62 (/light62	IBM_TDB USPAT;	2004/11/08 10:52
-	136	<pre>(((semiconductor\$3 & (light\$3 near3 emitt\$3)) & (higher same (thermal near3</pre>	USPAT; US-PGPUB;	2004/11/08 10:52
		expansion))) & (GaN (nitride adj bas\$3)))	EPO; JPO;	
		& substrate	DERWENT; IBM TDB	
_	94	((semiconductor\$3 & (light\$3 near3	USPAT;	2004/11/08 10:53
		emitt\$3)) & (higher same (thermal near3	US-PGPUB;	
		<pre>expansion))) & ((GaN (nitride adj bas\$3)) with substrate)</pre>	EPO; JPO; DERWENT;	
			IBM_TDB	
-	94		USPAT;	2004/11/08 10:54
		<pre>emitt\$3)) & (higher same (thermal near3 expansion))) & ((GaN (nitride adj bas\$3))</pre>	US-PGPUB; EPO; JPO;	
		with substrate)) & (layer\$1 chip\$3)	DERWENT;	,
1.			IBM_TDB	

r	17	((((semiconductor\$3 & (light\$3 near3	USPAT;	2004/11/08 11:25
_	1,	emitt\$3)) & (higher same (thermal near3	US-PGPUB;	2004/11/00 11.25
		expansion))) & ((GaN (nitride adj bas\$3).)	EPO; JPO;	
		with substrate)) & (layer\$1 chip\$3)) &	DERWENT;	
1		solder\$3	IBM TDB	
İ	7	"6326638"	USPAT;	2004/11/08 11:26
-	·	0320036	US-PGPUB;	2004/11/08 11:26
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/11/00 11:26
-	"	"6326638" & (thermal near3 expension)	USPAT;	2004/11/08 11:26
			US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	0004/41/00 44 07
-	2	"6326638" & solder\$3	USPAT;	2004/11/08 11:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
- '	2	("6326638" & solder\$3) & substrate	USPAT;	2004/11/08 13:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	